

SKM 400GA128D



SEMITRANS® 4

SPT IGBT Modules

SKM 400GA128D

Features

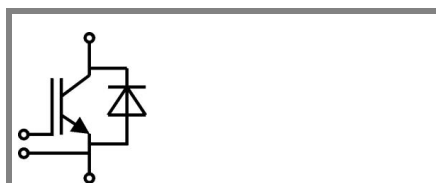
- SPT = Soft-Punch-Through technology
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

Typical Applications

- AC inverter drives
- UPS
- Electronic welders at f_{sw} up to 20 kHz

Remarks

- $I_{DC} \leq 500 \text{ A}$ for $T_{Terminal} = 100^\circ \text{C}$

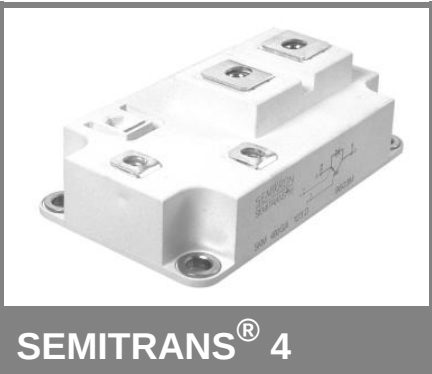


GA

Absolute Maximum Ratings		T _c = 25 °C, unless otherwise specified		
Symbol	Conditions		Values	Units
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	T _j = 150 °C	T _c = 25 °C	565	A
		T _c = 80 °C	400	A
I _{CRM}	I _{CRM} =2xI _{Cnom}		600	A
V _{GES}			± 20	V
t _{psc}	V _{CC} = 600 V; V _{GE} ≤ 20 V; T _j = 125 °C V _{CES} < 1200 V		10	µs
Inverse Diode				
I _F	T _j = 150 °C	T _{case} = 25 °C	390	A
		T _{case} = 80 °C	260	A
I _{FRM}	I _{FRM} =2xI _{Fnom}		600	A
I _{FSM}	t _p = 10 ms; sin. T _j = 150 °C		2900	A
Module				
I _{t(RMS)}			500	A
T _{vj}			- 40... + 150	°C
T _{stg}			- 40... + 125	°C
V _{isol}	AC, 1 min.		4000	V

Characteristics			T _C = 25°C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 12 mA		4,5	5,5	6,45	V	
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C			0,2	0,6	mA	
V _{CE0}	T _j = 25 °C			1	1,15	V	
	T _j = 125 °C			0,9	1,05	V	
r _{CE}	V _{GE} = 15 V T _j = 25°C			3	4	mΩ	
	T _j = 125°C			4	5	mΩ	
V _{CE(sat)}	I _{Cnom} = 300 A, V _{GE} = 15 V T _j = 25°C _{chiplev.}			1,9	2,35	V	
	T _j = 125°C _{chiplev.}			2,1	2,55	V	
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz		26			nF	
C _{oes}			3				nF
C _{res}			3				nF
Q _G	V _{GE} = -8V - +20V		3500			nC	
R _{Gint}	T _j = °C		1,25			Ω	
t _{d(on)}	R _{Gon} = 5 Ω	V _{CC} = 600V I _{Cnom} = 300A T _j = 125 °C V _{GE} = ±15V	120			ns	
t _r			70				ns
E _{on}			31				mJ
t _{d(off)}	800		ns				
t _f	75		ns				
E _{off}	R _{Goff} = 5 Ω		33			mJ	
R _{th(j-c)}		per IGBT		0,055		K/W	

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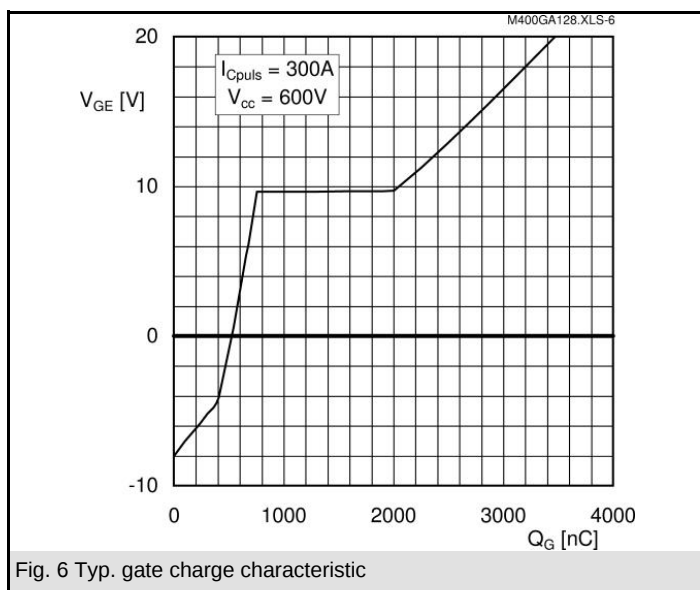
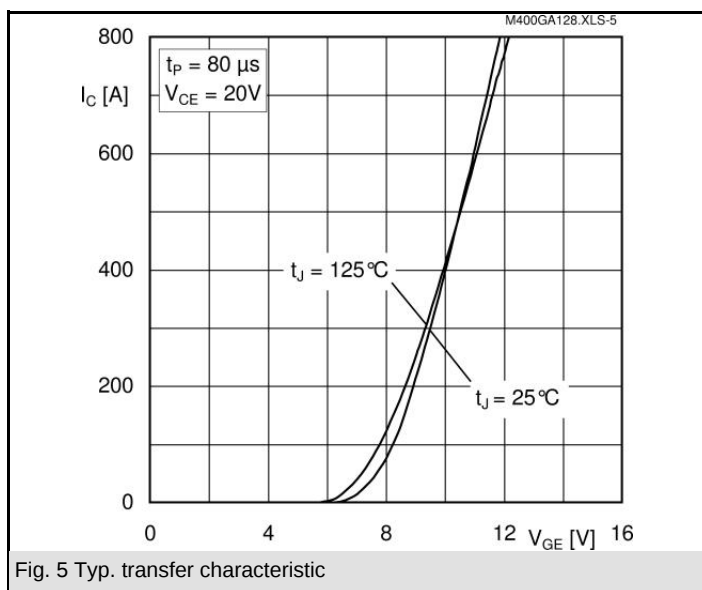
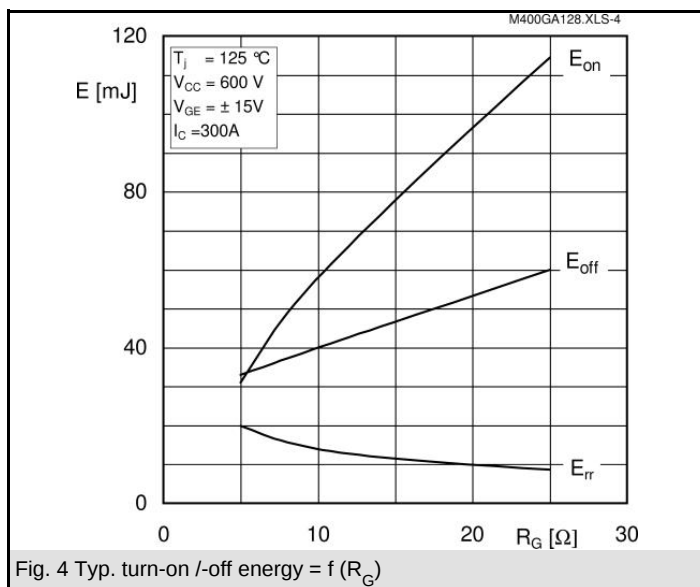
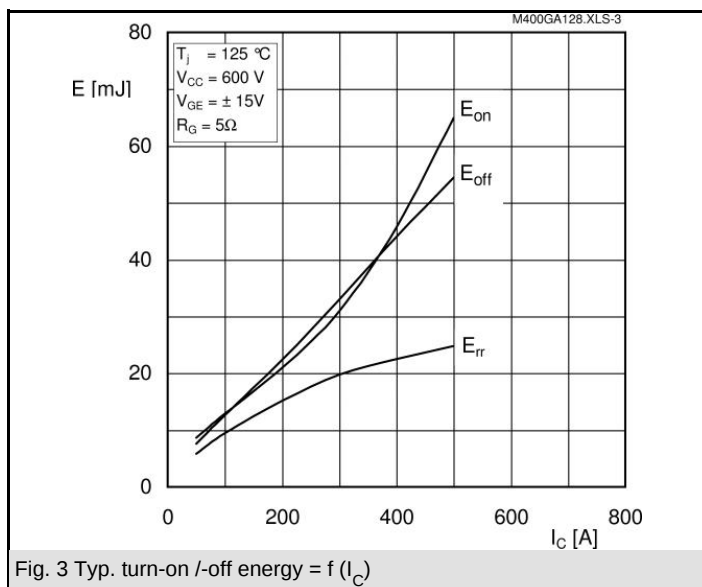
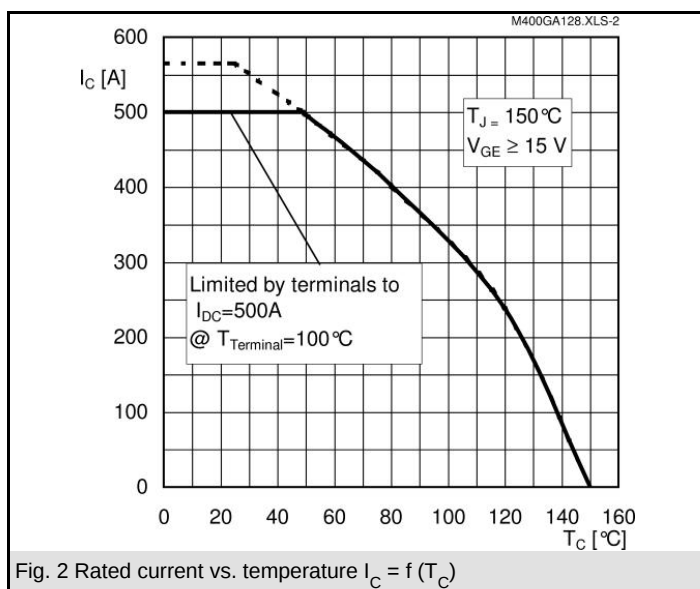
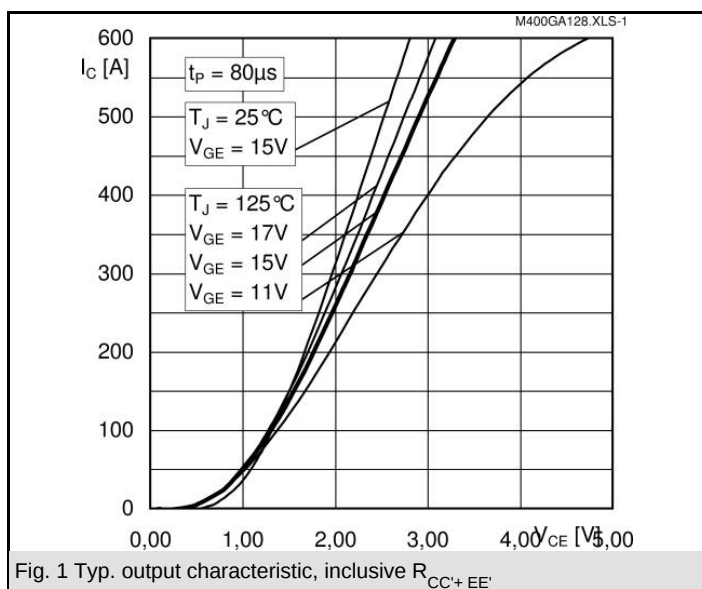
- $I_{DC} \leq 500 \text{ A}$ for $T_{Terminal} = 100 \text{ }^{\circ}\text{C}$

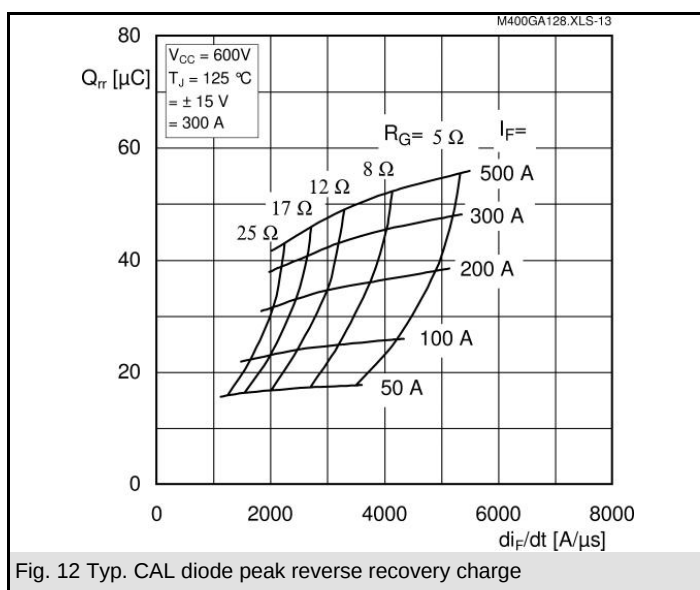
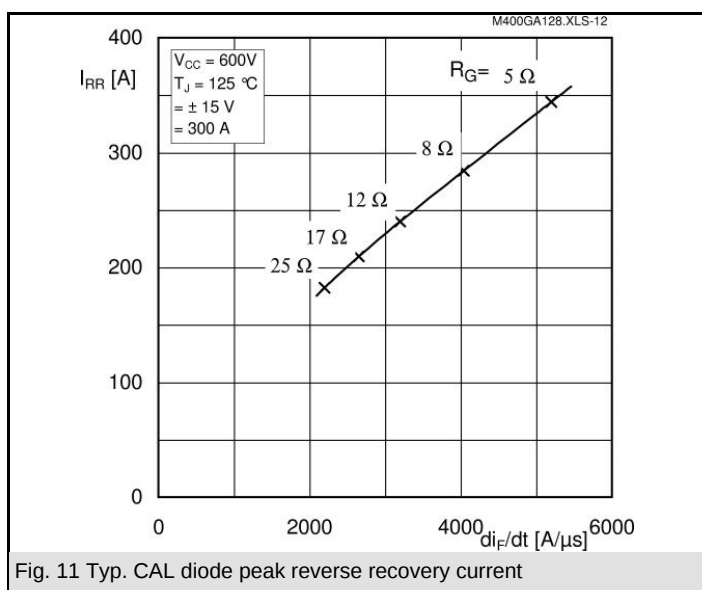
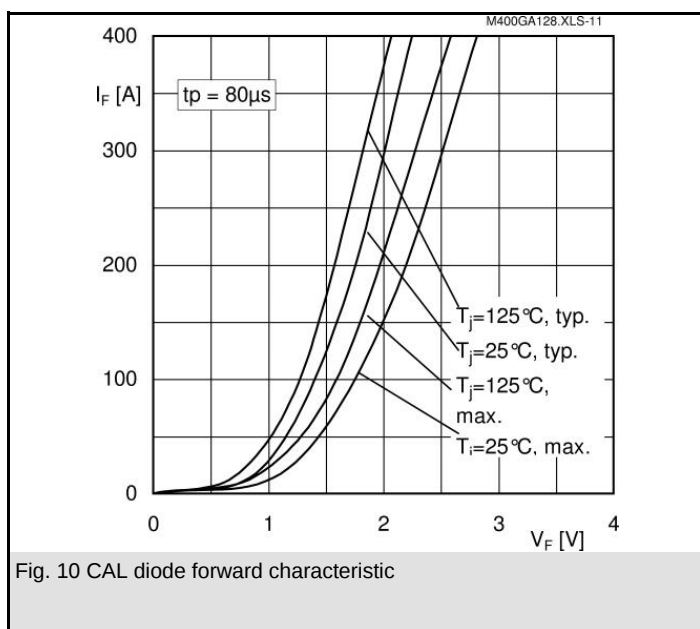
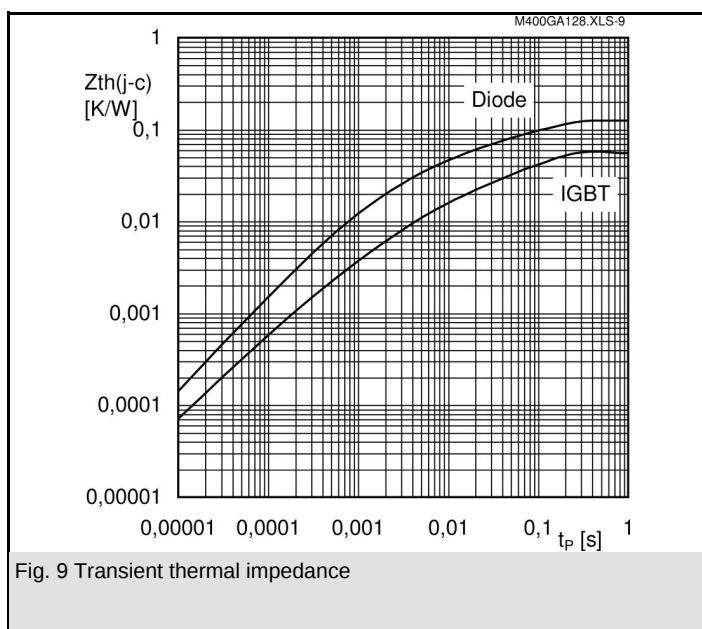
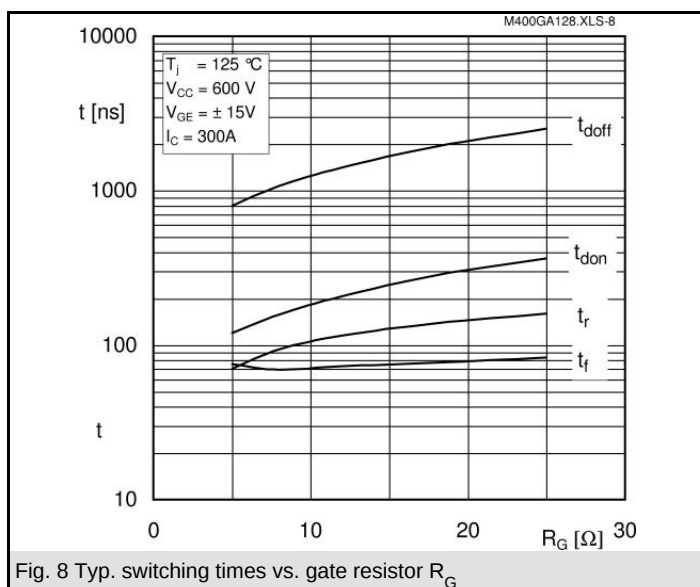
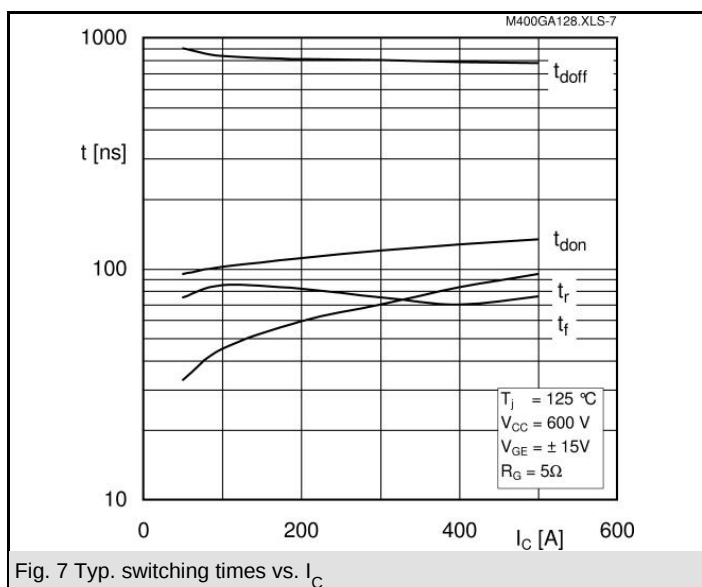


Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 300 \text{ A}; V_{GE} = 0 \text{ V}$ $T_j = 25 \text{ }^{\circ}\text{C}_{chiplev.}$ $T_j = 125 \text{ }^{\circ}\text{C}_{chiplev.}$		2 1,8	2,5	V V
V_{F0}	$T_j = 25 \text{ }^{\circ}\text{C}$		1,1	1,2	V
r_F	$T_j = 25 \text{ }^{\circ}\text{C}$		3	4,3	mΩ
I_{RRM} Q_{rr} E_{rr}	$I_{Fnom} = 300 \text{ A}$ $di/dt = 5200 \text{ A}/\mu\text{s}$ $V_{GE} = -15 \text{ V}; V_{CC} = 600 \text{ V}$ $T_j = 125 \text{ }^{\circ}\text{C}$		345 48 20		A μC mJ
$R_{th(j-c)D}$	per diode			0,125	K/W
Module					
L_{CE}			15	20	nH
$R_{CC'+EE'}$	res., terminal-chip $T_{case} = 25 \text{ }^{\circ}\text{C}$ $T_{case} = 125 \text{ }^{\circ}\text{C}$		0,18 0,22		mΩ mΩ
$R_{th(c-s)}$	per module			0,038	K/W
M_s	to heat sink M6	3		5	Nm
M_t	to terminals M6 (M4)	2,5 (1,1)		5 (2)	Nm
w				330	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.





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